



Stud Diode

Rectifier Diode

SKN 26
SKR 26

Features

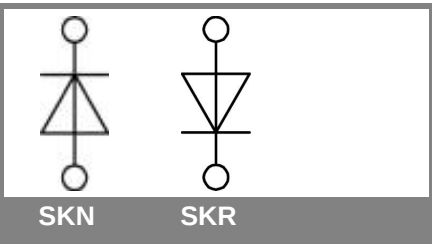
- Reverse voltages up to 1600 V
- Hermetic metal case with glass insulator
- Threaded stud ISO M6 (SKR 26 also 10 - 32 UNF)
- SKN: anode to stud, SKR: cathode to stud

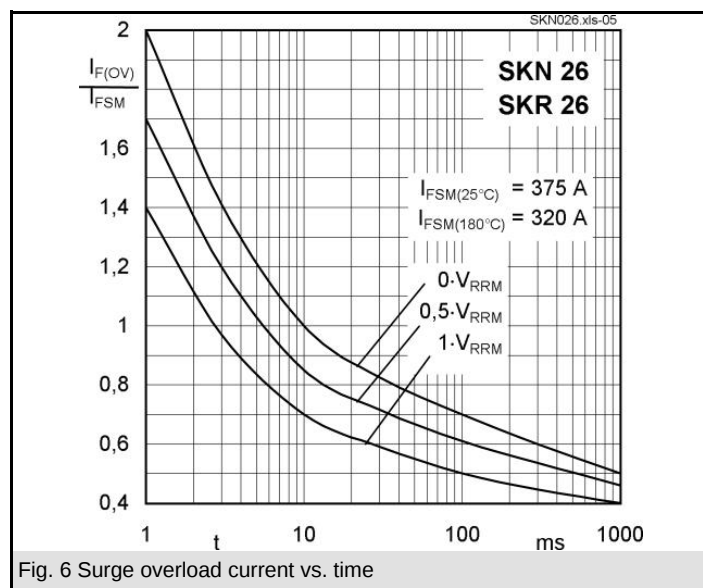
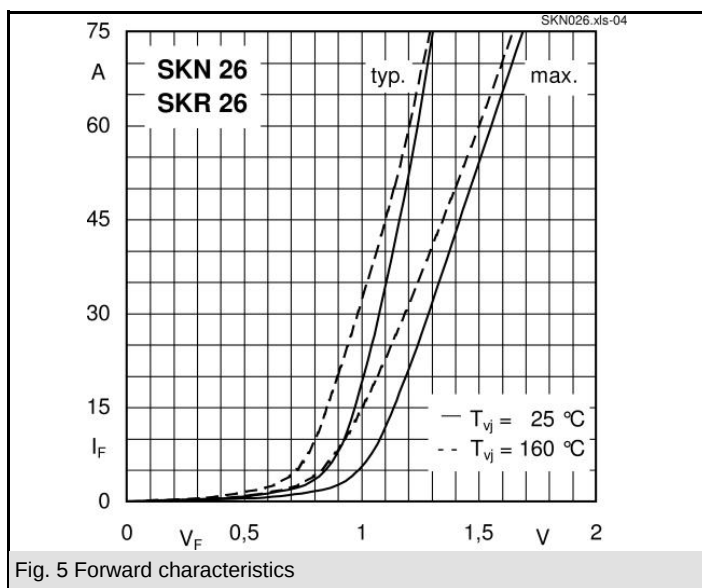
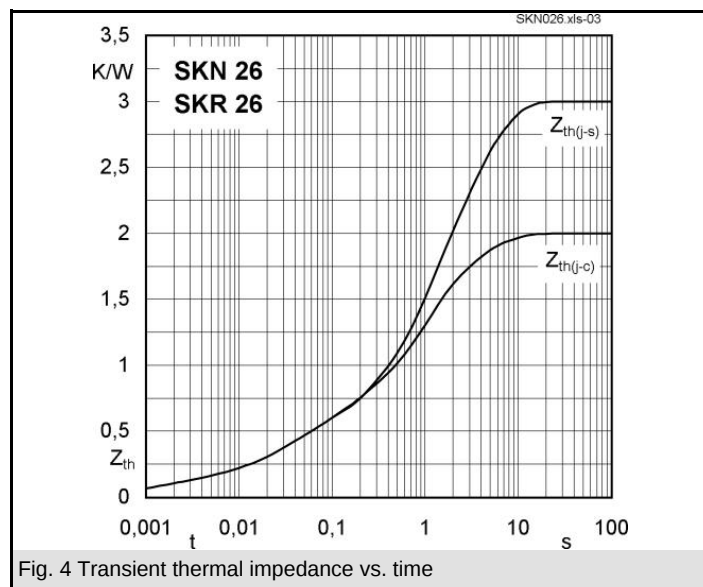
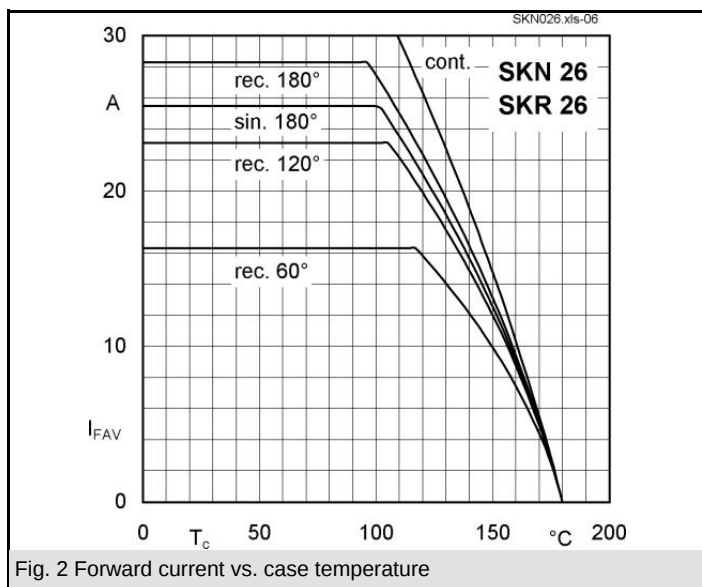
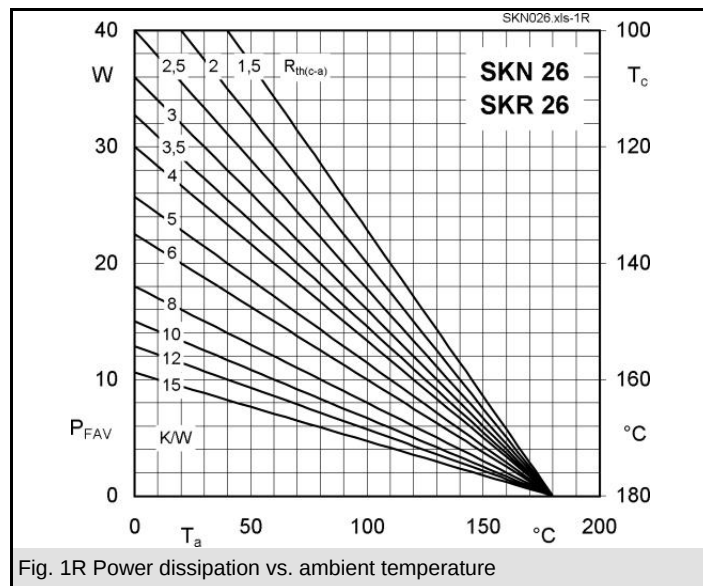
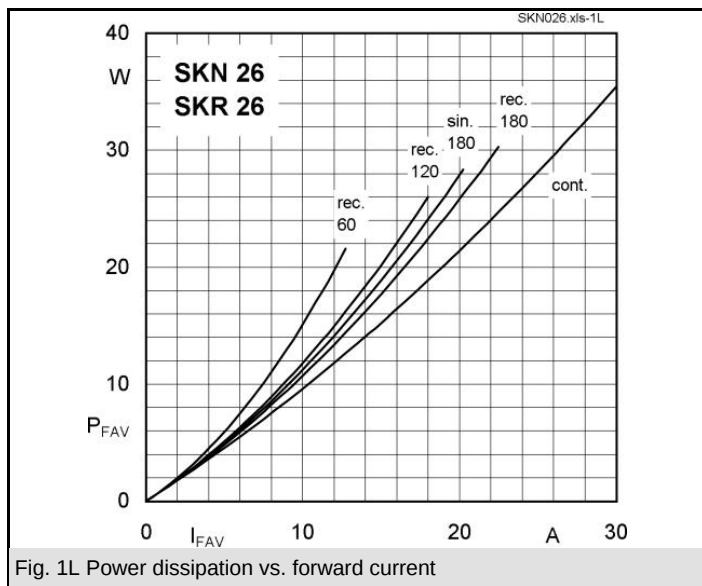
Typical Applications

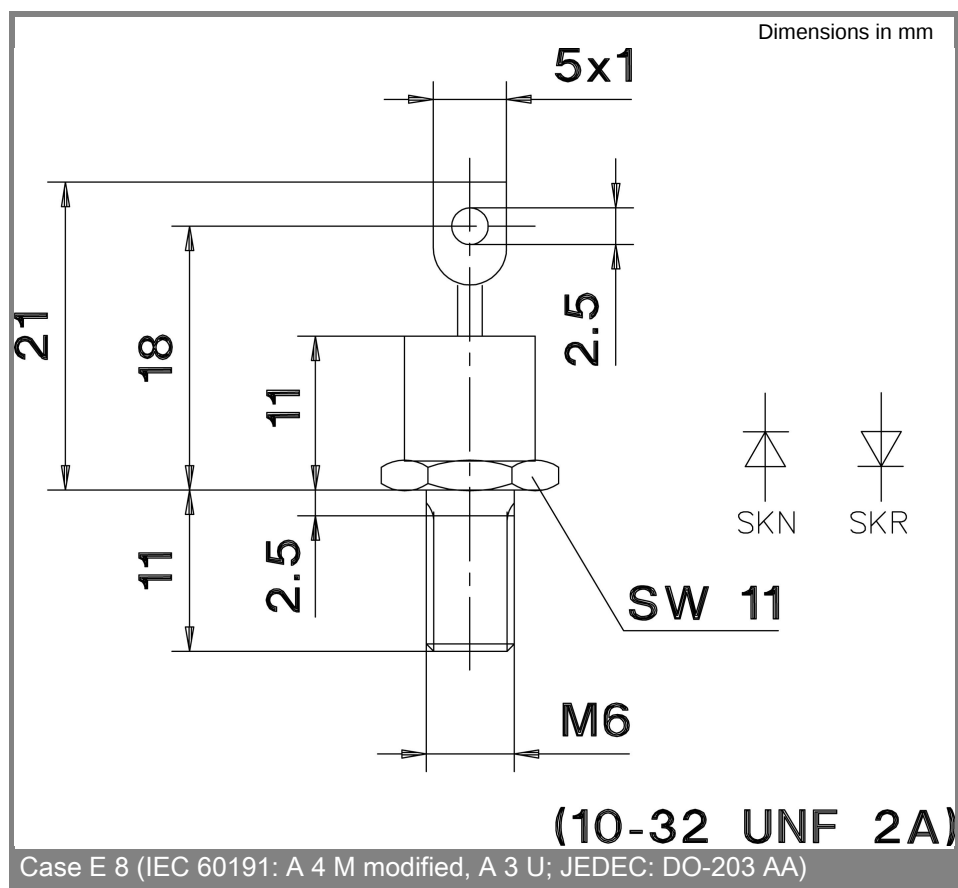
- All-purpose mean power rectifier diodes
- Cooling via metal plates or heatsinks
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes
- Recommended snubber network:
RC: 0,05 µF, 200 Ω (P_R = 1 W),
R_P = 150 kΩ (P_R = 4 W)

V _{RSM} V	V _{RRM} V	I _{FRMS} = 40 A (maximum value for continuous operation)		
		I _{FAV} = 25 A (sin. 180 °; T _c = 100 °C)		
400	400	SKN 26/04	SKR 26/04	
800	800	SKN 26/08	SKR 26/08	
1200	1200	SKN 26/12	SKR 26/12	
1400	1400	SKN 26/14	SKR 26/14	
1600	1600	SKN 26/16	SKR 26/16	

Symbol	Conditions	Values	Units
I _{FAV}	sin. 180; T _c = 100 °C	25	A
I _D	K 9; T _a = 45 °C; B2 / B6	20 / 29	A
	K 3; T _a = 45 °C; B2 / B6	35 / 50	A
I _{FSM}	T _{vj} = 25 °C; 10 ms	375	A
	T _{vj} = 180 °C; 10 ms	320	A
i ² t	T _{vj} = 25 °C; 8,3 ... 10 ms	700	A²s
	T _{vj} = 180 °C; 8,3 ... 10 ms	510	A²s
V _F	T _{vj} = 25 °C; I _F = 60 A	max. 1,55	V
V _(TO)	T _{vj} = 180 °C	max. 0,85	V
r _T	T _{vj} = 180 °C	max. 11	mΩ
I _{RD}	T _{vj} = 180 °C; V _{RD} = V _{RRM}	max. 4	mA
Q _{rr}	T _{vj} = 160 °C; - di _F /dt = 10 A/µs	20	µC
R _{th(j-c)}		2	K/W
R _{th(c-s)}		1	K/W
T _{vj}		- 40 ... + 180	°C
T _{stg}		- 55 ... + 180	°C
V _{isol}		-	V~
M _s	to heatsink	2,0	Nm
a		5 * 9,81	m/s²
m	approx.	8	g
Case		E 8	







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